

INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)

Docket Number (Optional)

SETI-0001

Application Number

09/966563

Applicant(s)

Khan et al.

Filing Date

September 27, 2001

Group Art Unit

2814

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

FOREIGN PATENT DOCUMENTS

	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

FB		"The Influence of the Strain-Induced Electric Field on the Charge Distribution in GaN-AlN-GaN Structure," A. D. Bykhovski et al., Journal of Applied Physics, Vol. 74, No. 11, December 1, 1993, pp.6734-6739.
PK		"Pyroelectricity in Gallium Nitride Thin Films," A. D. Bykhovski et al., Applied Physics Letters, Vol. 69, No. 21, November 18, 1996, pp. 3254-3256.

EXAMINER

fmh *for 6/20/01*

DATE CONSIDERED

03/09/05

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)

Docket Number (Optional)

SETI-0001

Application Number

09/966563

Applicant(s)

Khan et al.

Filing Date

September 27, 2001

Group Art Unit

2814

*EXAMINER
INITIAL

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

PE

"Pyroelectric and Piezoelectric Properties of GaN-Based Materials," M. S. Shur et al., MRS Internet J. Nitride Semicond. Res. 4S1, G1.6 (1999), pp. 1-12.

"Piezoeffect and Gate Current in AlGaIn/GaN High Electron Mobility Transistors," R. Gaska et al., Applied Physics Letters, Vol. 71, No. 25, December 22, 1997, pp. 3673-3675.

"Two-Dimensional Electron-Gas Density in AlxGa1-xN/GaN Heterostructure Field-Effect Transistors," N. Maeda et al., Applied Physics Letters, Vol. 73, No. 13, September 28, 1998, pp. 1856-1858.

"Piezoelectric Charge Densities in AlGaIn/GaN HFETs," P.M. Asbeck et al., Electronic Letters, Vol. 33, No. 14, July 3, 1997, 1230-1231.

"Spontaneous Polarization and Piezoelectric Constants of III-V Nitrides," F. Bernardini et al., Physical Review B, Vol. 56, No. 16, October 15, 1997, pp. R10024-R10027.

"Piezoelectric Doping and Elastic Strain Relaxation in AlGaIn-GaN Heterostructure Field Effect Transistors," A. D. Bykhovski et al., Applied Physics Letters, Vol. 73, No. 24, December 14, 1998, pp. 3577-3579.

"Ferroelectric Semiconductors," V. M. Fridkin, Russia (1976), p. 90 (pp. 64-65 in English version).

"Lattice and Energy Band Engineering in AlInGaIn/GaN Heterostructures," M. A. Khan et al., Applied Physics Letters, Vol. 76, No. 9, February 28, 2000, pp. 1161-1163.

"Electron Mobility in Modulation-Doped AlGaIn-GaN Heterostructures," R. Gaska et al., Applied Physics Letters, Vol. 74, No. 2, January 11, 1999, pp. 287-289.

"High Pinch-off Voltage AlGaIn-GaN Heterostructure Field Effect Transistor," M. S. Shur et al., Proceedings of ISDRS-97, Charlottesville, VA, December 1997, pp. 377-380.

"Optoelectronic GaN-Based Field Effect Transistors," M. S. Shur et al., SPIE Vol. 2397, pp. 294-303.

"Current/Voltage Characteristic Collapse in AlGaIn/GaN Heterostructure Insulated Gate Field Effect Transistors at High Drain Bias," M. A. Khan et al., Electronic Letters, Vol. 30, No. 25, December 8, 1994, pp. 2175-2176.

EXAMINER

John R. Smith

DATE CONSIDERED

03/09/05

*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.